



T16M25F800HD(LS)

TRIACS SILICON BIDIRECTIONAL THYRISTORS

TRIACS 16 AMPERES RMS 800V VOLTS

FEATURES

- High voltage capability
- High junction operating temperature capability
- · Triggering in all four quadrants
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

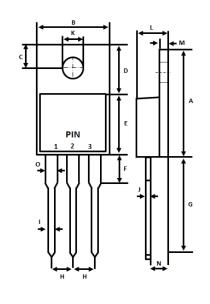
APPLICATIONS

- · Applications subject to high temperature
- · Heating and cooking appliances
- · Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum

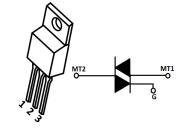
MECHANICAL DATA

- Package: TO-220AB Insulated
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 2.15 grams (Approximate)

TO-220AB Insulated



TO 000 A D				
TO-220AB Insulated				
DIM.	MIN.	MAX		
Α	14.40	15.20		
В	9.65	10.67		
С	2.54	3.43		
D	5.84	6.86		
Е	8.26	9.28		
F	-	6.35		
G	12.7	14.73		
Н	2.29	2.79		
ı	0.51	1.14		
J	0.30	0.64		
K	3.53Ø	4.09Ø		
L	3.56	4.83		
М	1.14	1.40		
N	2.03	2.92		
0	1.14	1.37		
All dimensions in				
millimeter				



PIN ASSIGNMENT			
1	Main terminal 1		
2	Main terminal 2		
3	Gate		

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at +25°C ambient temperature unless otherwise specified.

PARAMETER	SYMBOL	VALUE	UNIT
Peak repetitive off-state voltage (T _J = -40 to +150°C, full sine wave, 50 to 60Hz, gate open)	V _{DRM} V _{RRM}	800 800	V
On-stage RMS current (full sine wave, T _C = +125°C)	I _{T(RMS)}	16	Α
Peak non-repetitive surge current (full sine wave @ 50Hz, T _J = +25°C)	I _{TSM}	160	Α
Circuit fusing consideration (t = 10ms)	l ² t	128	A ² s
Operating junction temperature range	TJ	-40 to +150	°C
Storage temperature range	T _{STG}	-40 to +150	°C

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



RATING AND CHARACTERISTIC CURVES T16M25F800HD

OFF CHARACTERISTICS

PARAMETER		SYMBOL	MAX	UNIT
Peak repetitive forward or reverse blocking current	T _J = +25°C	I _{DRM} I _{RRM}	5	μΑ
$(V_{AK} = \text{rated } V_{DRM} \text{ and } V_{RRM}, \text{ gate open})$	T _J = +150°C		2	mA

ON CHARACTERISTICS

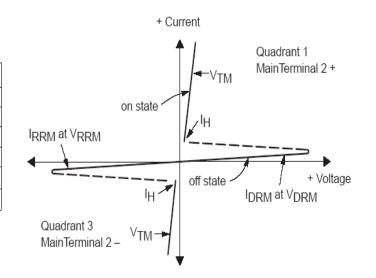
PARAMETER	SYMBOL	MAX	UNIT
Peak forward on-state voltage (I _{TM} = 16A @ T _J = +25°C)	V _{TM}	1.55	V
Gate trigger current ($V_{AK} = 12V$, $R_L = 100\Omega$)	I _{GT} 1 I _{GT} 2 I _{GT} 3 I _{GT} 4	25 25 25 50	mA
Gate trigger voltage ($V_{AK} = 12V$, $R_L = 100\Omega$)	V _{GT} 1 V _{GT} 2 V _{GT} 3 V _{GT} 4	1.3	V
Holding current ($V_{AK} = 12V$, $R_L = 100\Omega$)	Iн1 Iн3	25	mA
Latching current ($V_{AK} = 12V$, $R_L = 100\Omega$)	IL1 IL2 IL3 IL4	40 80 40 40	mA

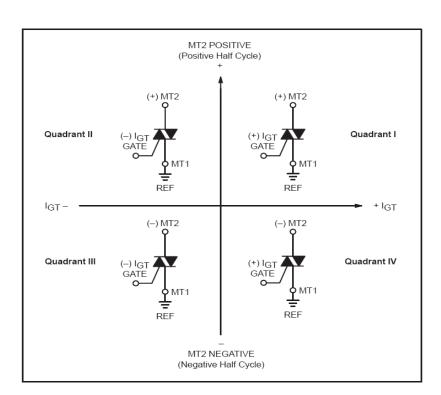
DYNAMIC CHARACTERISTICS

PARAMETER	SYMBOL	MIN.	UNIT
Critical rate of rise of off-stage voltage ($V_{AK} = 67\%$ rated V_{DRM} , exponential waveform, gate open, $T_J = +125$ °C)	dv/dt(s)	200	V/µs
Critical rate of rise of on-state current $(V_{DRM} = maximum V_{DRM}, T_J = +125^{\circ}C)$	di/dt(s)	60	A/µs
Rate of change of commutating current ($V_D = 400V$, $5V/\mu s$, $T_J = +125$ °C)	di/dt(c)	7.0	A/ms

RATING AND CHARACTERISTIC CURVES T16M25F800HD

Symbol	Parameter
VDRM	Peak Repetitive Forward Off State Voltage
IDRM	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
IRRM	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
lΗ	Holding Current

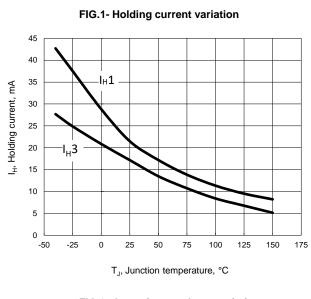




All polarities are reference to MT1, with in-phase signal (using standard AC lines) quadrants I and III are used.



RATING AND CHARACTERISTIC CURVES T16M25F800HD





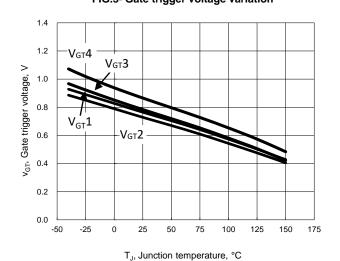


FIG.5- On-state characteristics

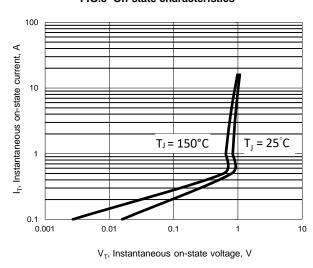
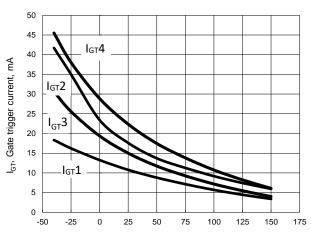
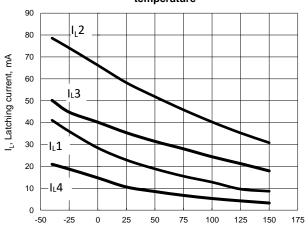


FIG.2- Gate trigger current variation



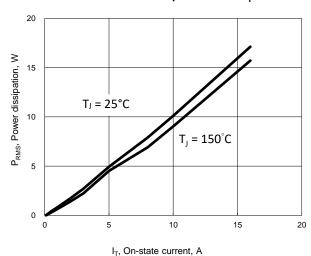
T_J, Junction temperature, °C

FIG.4- Typical latching current versus junction temperature

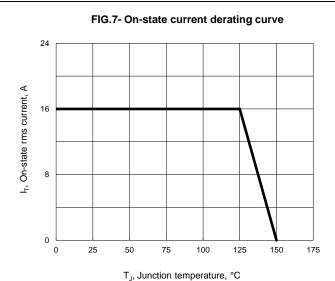


 T_J , Junction temperature, °C

FIG.6- Power dissipation versus I_T



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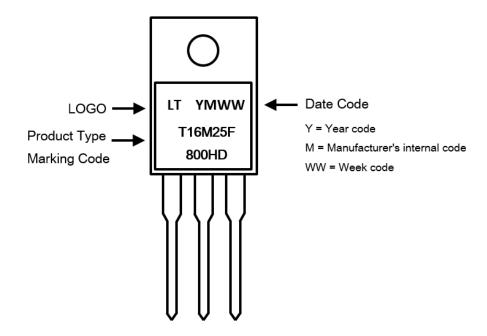




Ordering Information:

Part Number	Packago	Packing		
rait Nullibei	Package	Qty.	Carrier	
T16M25F800HD	TO-220AB Insulated	50pcs	Tube	

Marking Information:





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